

# MJL3281A (NPN) MJL1302A (PNP)

## Complementary Bipolar Power Transistors

### Features

- Exceptional Safe Operating Area
- NPN/PNP Gain Matching within 10% from 50 mA to 5 A
- Excellent Gain Linearity
- High BVCEO
- High Frequency
- These Devices are Pb-Free and are RoHS Compliant\*

### Benefits

- Reliable Performance at Higher Powers
- Symmetrical Characteristics in Complementary Configurations
- Accurate Reproduction of Input Signal
- Greater Dynamic Range
- High Amplifier Bandwidth

### Applications

- High-End Consumer Audio Products
  - ◆ Home Amplifiers
  - ◆ Home Receivers
- Professional Audio Amplifiers
  - ◆ Theater and Stadium Sound Systems
  - ◆ Public Address Systems (PAs)

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	260	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	260	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector-Emitter Voltage - 1.5 V	V <sub>CEX</sub>	260	Vdc
Collector Current - Continuous	I <sub>C</sub>	15	Adc
Collector Current - Peak (Note 1)	I <sub>CM</sub>	25	Adc
Base Current - Continuous	I <sub>B</sub>	1.5	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate Above 25°C	P <sub>D</sub>	200 1.43	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 65 to +150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	0.625	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

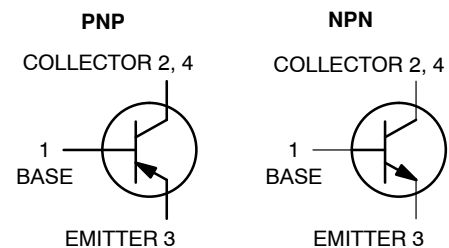
1. Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.



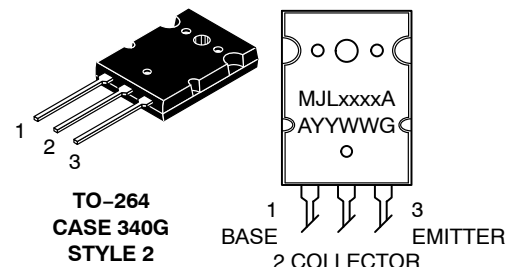
**ON Semiconductor®**

<http://onsemi.com>

**15 AMPERES  
COMPLEMENTARY  
SILICON POWER  
TRANSISTORS  
260 VOLTS  
200 WATTS**



### MARKING DIAGRAM



xxxx = 3281 or 1302  
A = Location Code  
YY = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping
MJL3281AG	TO-264 (Pb-Free)	25 Units/Rail
MJL1302AG	TO-264 (Pb-Free)	25 Units/Rail

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## MJL3281A (NPN) MJL1302A (PNP)

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

#### OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 100 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	260	–	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = 260 V <sub>dc</sub> , I <sub>E</sub> = 0)	I <sub>CBO</sub>	–	50	μA <sub>dc</sub>
Emitter Cutoff Current (V <sub>EB</sub> = 5 V <sub>dc</sub> , I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	5	μA <sub>dc</sub>

#### SECOND BREAKDOWN

Second Breakdown Collector with Base Forward Biased (V <sub>CE</sub> = 50 V <sub>dc</sub> , t = 1 s (non–repetitive)) (V <sub>CE</sub> = 100 V <sub>dc</sub> , t = 1 s (non–repetitive))	I <sub>S/b</sub>	4 1	– –	A <sub>dc</sub>
--	------------------	--------	--------	-----------------

#### ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = 500 mA <sub>dc</sub> , V <sub>CE</sub> = 5 V <sub>dc</sub> ) (I <sub>C</sub> = 1 A <sub>dc</sub> , V <sub>CE</sub> = 5 V <sub>dc</sub> ) (I <sub>C</sub> = 3 A <sub>dc</sub> , V <sub>CE</sub> = 5 V <sub>dc</sub> ) (I <sub>C</sub> = 5 A <sub>dc</sub> , V <sub>CE</sub> = 5 V <sub>dc</sub> ) (I <sub>C</sub> = 8 A <sub>dc</sub> , V <sub>CE</sub> = 5 V <sub>dc</sub> )	h <sub>FE</sub>	75 75 75 75 45	150 150 150 150 –	
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 A <sub>dc</sub> , I <sub>B</sub> = 1 A <sub>dc</sub> )	V <sub>CE(sat)</sub>	–	3	V <sub>dc</sub>

#### DYNAMIC CHARACTERISTICS

Current–Gain – Bandwidth Product (I <sub>C</sub> = 1 A <sub>dc</sub> , V <sub>CE</sub> = 5 V <sub>dc</sub> , f <sub>test</sub> = 1 MHz)	f <sub>T</sub>	30	–	MHz
Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)	C <sub>ob</sub>	–	600	pF

# MJL3281A (NPN) MJL1302A (PNP)

## TYPICAL CHARACTERISTICS

PNP MJL1302A

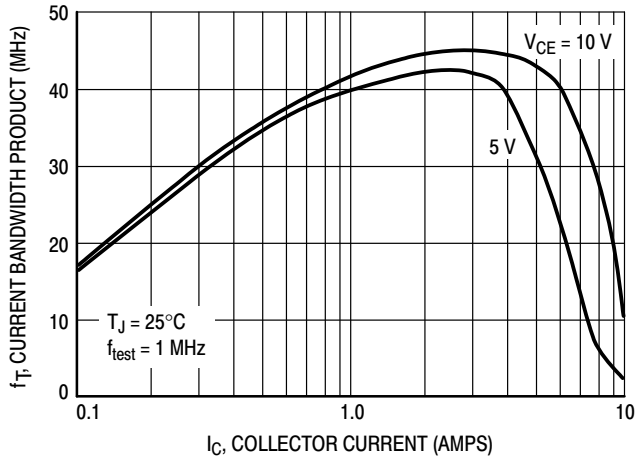


Figure 1. Typical Current Gain Bandwidth Product

NPN MJL3281A

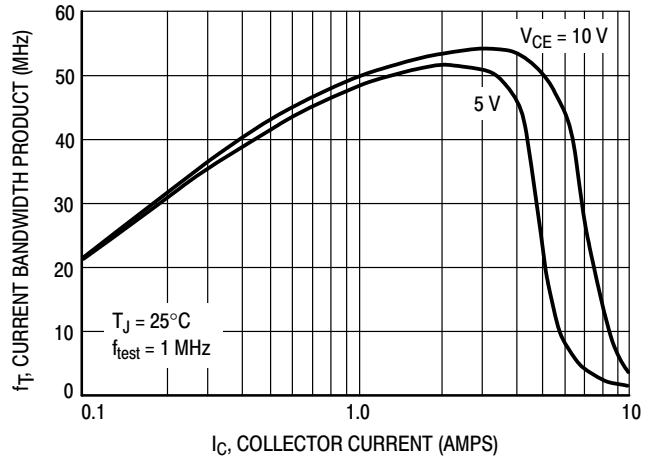


Figure 2. Typical Current Gain Bandwidth Product

PNP MJL1302A

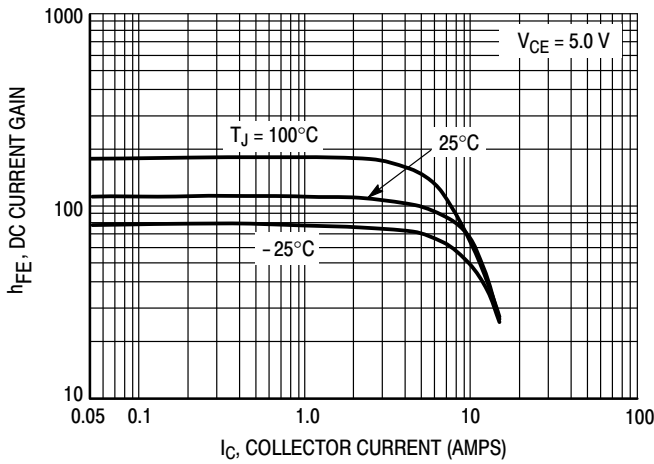


Figure 3. DC Current Gain

NPN MJL3281A

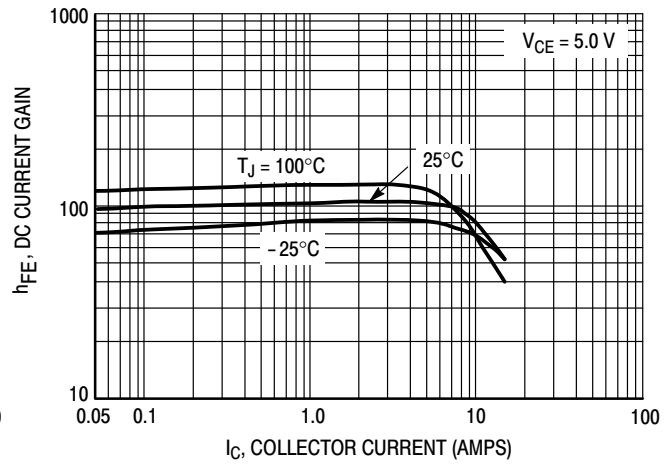


Figure 4. DC Current Gain

PNP MJL1302A

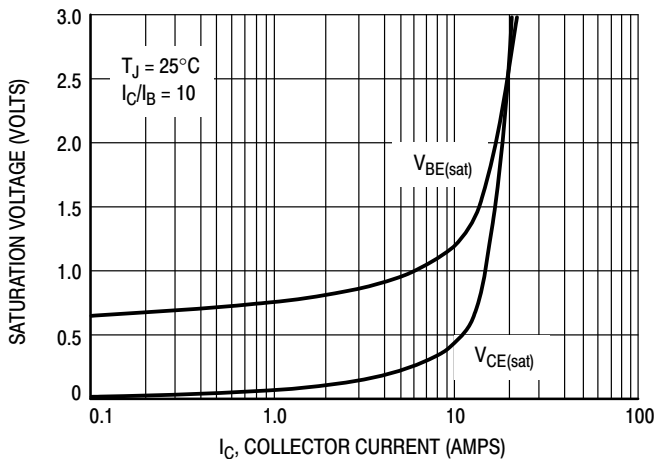


Figure 5. Typical Saturation Voltages

NPN MJL3281A

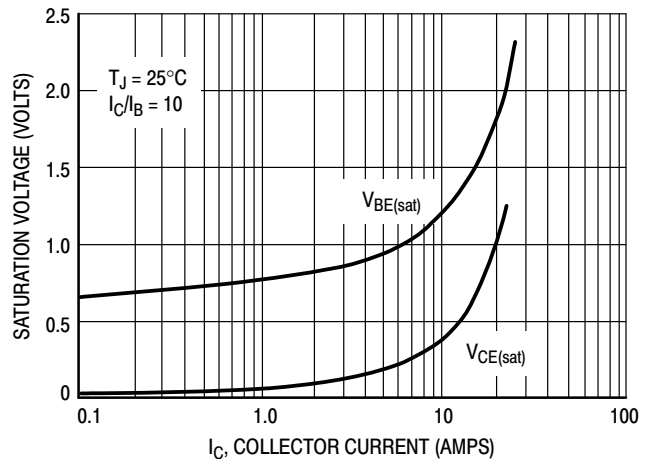


Figure 6. Typical Saturation Voltages

# MJL3281A (NPN) MJL1302A (PNP)

## TYPICAL CHARACTERISTICS

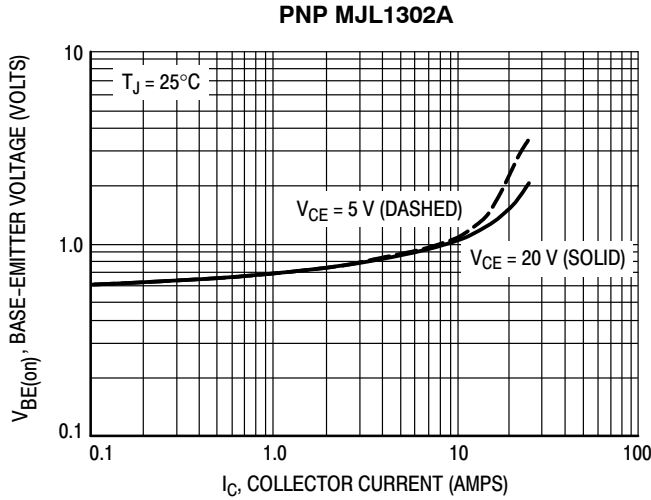


Figure 7. Typical Base-Emitter Voltage

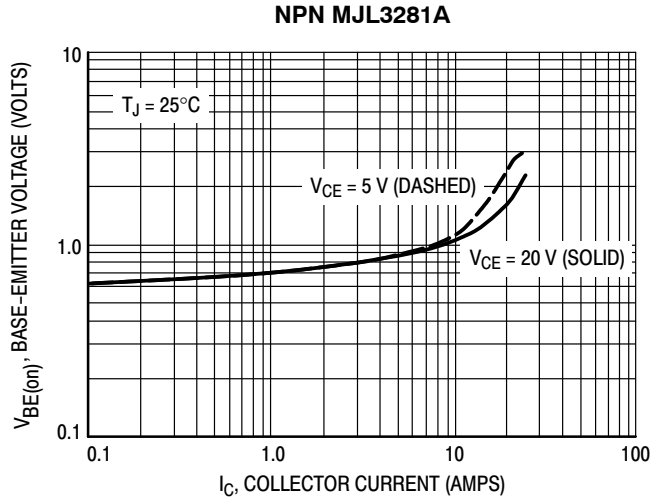


Figure 8. Typical Base-Emitter Voltage

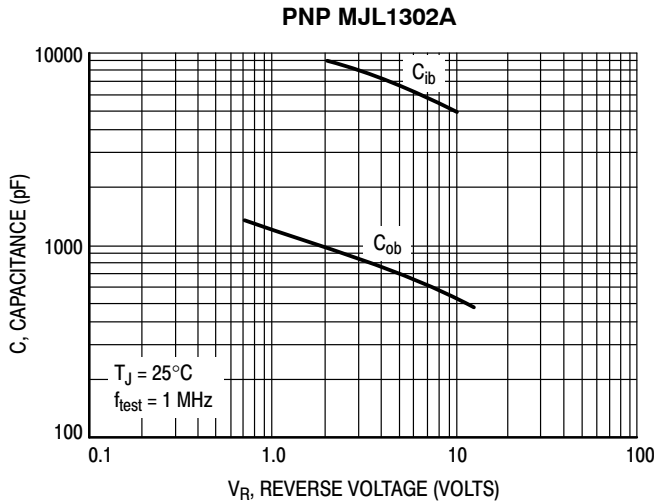


Figure 9. MJL1302A Typical Capacitance

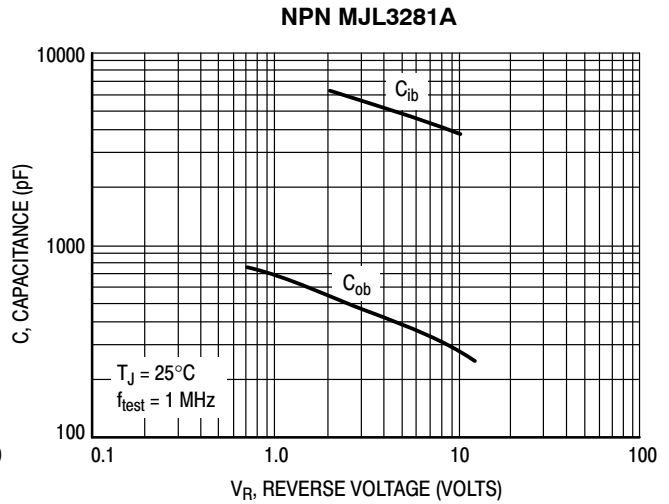


Figure 10. MJL3281A Typical Capacitance

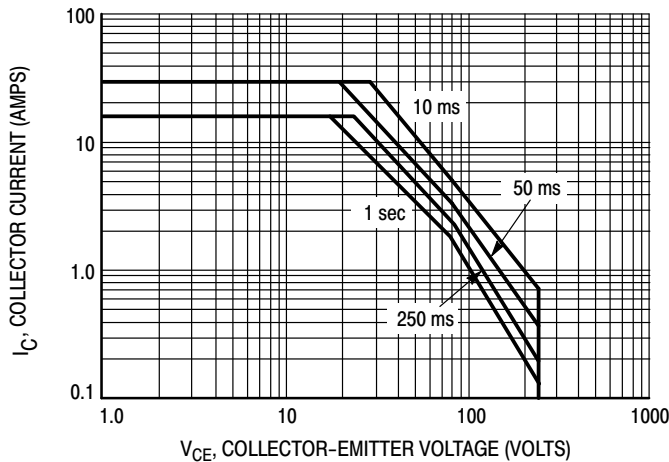


Figure 11. Active Region Safe Operating Area

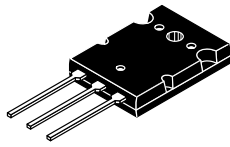
There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 11 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

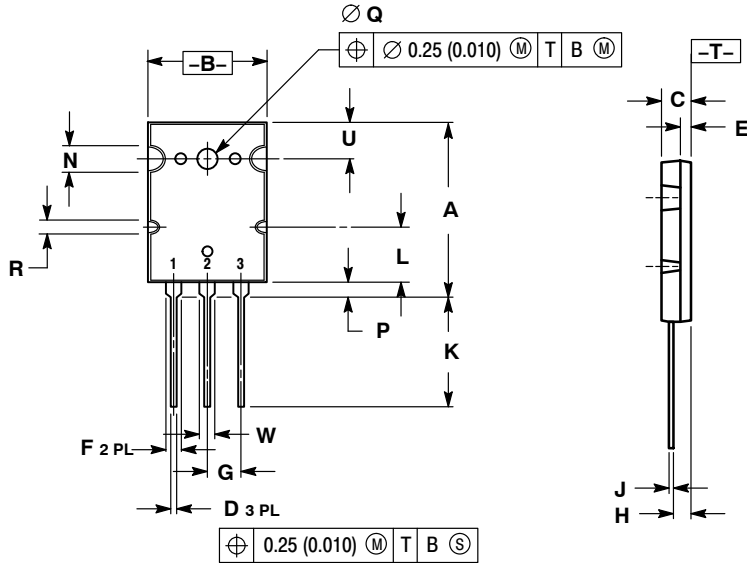
ON Semiconductor®



TO-3BPL (TO-264)  
CASE 340G-02  
ISSUE J

DATE 17 DEC 2004

SCALE 1:2

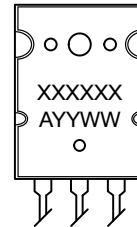


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	28.0	29.0	1.102	1.142
B	19.3	20.3	0.760	0.800
C	4.7	5.3	0.185	0.209
D	0.93	1.48	0.037	0.058
E	1.9	2.1	0.075	0.083
F	2.2	2.4	0.087	0.102
G	5.45 BSC		0.215 BSC	
H	2.6	3.0	0.102	0.118
J	0.43	0.78	0.017	0.031
K	17.6	18.8	0.693	0.740
L	11.2 REF		0.411 REF	
N	4.35 REF		0.172 REF	
P	2.2	2.6	0.087	0.102
Q	3.1	3.5	0.122	0.137
R	2.25 REF		0.089 REF	
U	6.3 REF		0.248 REF	
W	2.8	3.2	0.110	0.125

### GENERIC MARKING DIAGRAM\*

- |  |   |  |  |   |
|--|---|--|--|---|
| STYLE 1:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE | STYLE 2:<br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER | STYLE 3:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN | STYLE 4:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE | STYLE 5:<br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER |
|--|---|--|--|---|



- XXXXXX = Specific Device Code
- A = Location Code
- YY = Year
- WW = Work Week

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

DOCUMENT NUMBER:	98ASB42780B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-3BPL (TO-264)	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

---

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at [www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)